

DESCRIPTION:

The products are transistor opto-couplers in a plastic SOP4 package. The device combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector. With the robust coplanar double mold structure, the device provides the most stable isolation feature. The products are widely used in switch mode power supplies, programmable controllers, household appliances and office equipment.

MAIN FEATURES

High isolation 3750 VRMS

Operating temperature range -40°C to 125°C

RoHS & REACH Compliance

HBM: H3A; MM: M4; CDM:C3

CQC approved

VDE approved

UL approved



ABSOLUTE MAXIMUM RATINGS (Temperature=25°C)

Parameter		Symbol	Value	Unit
Input	Forward Current	I_F	50	mA
	Peak Forward Current	I_{FP}	1 ^①	A
	Reverse Voltage	V_R	6	V
	Power Dissipation	P_D	75	mW
Output	Collector-emitter Voltage	V_{CEO}	80	V
	Emitter-collector Voltage	V_{ECO}	7	V
	Collector Current	I_C	50	mA
	Power Dissipation	P_C	150	mW
Total Power Dissipation		P_{tot}	225	mW
Isolation Voltage		V_{iso}	3750 ^②	Vrms
Operating Temperature		T_{opr}	-40~+125	°C
Junction Temperature		T_j	135	°C
Storage Temperature		T_{stg}	-55~+125	°C

Soldering Temperature	T_{sol}	260	°C
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NOTE1: 100 μ s pulse, 100Hz frequency

NOTE2: AC for 1minute, R.H.=40~60%

ELECTRICAL CHARACTERISTICS (Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V_F	$I_F=10mA$	-	1.2	1.5	V
	Reverse Current	I_R	$V_R=6V$	-	-	1	μA
	Terminal Capacitance	C_t	$V=0,$ $f=1MHz$	-	10	-	pF
Output	Collector-Emitter dark current	I_{CEO}	$V_{CE}=20V,$ $I_F=0$	-	-	100	nA
	Collector-Emitter breakdown voltage	BV_{CEO}	$I_C=0.1mA$ $I_F=0$	80	-	-	V
	Emitter-Collector breakdown voltage	BV_{ECO}	$I_E=0.1mA$ $I_F=0$	7	-	-	V
Transfer Characteristics	Current transfer ratio	CTR ^①	$I_F=5mA$ $V_{CE}=5V$	100	-	400	%
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_F=20mA$ $I_C=1mA$	-	0.06	0.2	V
	Isolation resistance	R_{IO}	DC500V 40~60%R.H.	10^{12}	10^{14}	-	Ω
	Floating Capacitance	C_{IO}	$V=0,$ $f=1MHz$	-	0.4	1	pF
	Cut-off Frequency	f_c	$V_{CE}=5V,$ $I_C=2mA$ $R_L=100\Omega,$ -3dB	-	80	-	kHz
	Rise Time	t_r	$V_{CE}=2V,$ $I_C=2mA$ $R_L=100\Omega$	-	3	18	μs
	Fall Time	t_f		-	4	18	μs
	Response Time	t_{on}		-	6	25	μs
t_{off}		-		5	25	μs	

NOTE1: Rank Table of Current Transfer Ratio (Temperature=25°C)

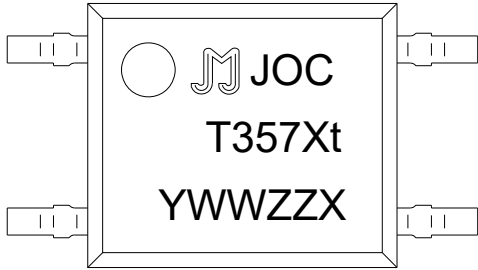
CTR Rank	Min. (%)	Max. (%)	Test Condition
P	200	400	$I_F=0.5mA, V_{CE}=5V$
	200	400	$I_F=5mA, V_{CE}=5V$
Q	100	300	$I_F=0.5mA, V_{CE}=5V$
	100	300	$I_F=5mA, V_{CE}=5V$

ORDERING INFORMATION

<p><u>J</u></p> <p>JieJie Microelectronics Co., Ltd.</p>	<p><u>OC</u></p> <p>Opto Coupler</p>	<p><u>T</u></p> <p>Transistor</p>	<p><u>357</u></p> <p>Marketization Model</p>	<p><u>P</u></p> <p>CTR Rank:P/Q</p>	<p><u>t</u></p> <p>t: High Temperature</p>	<p><u>-M4</u></p> <p>SOP4</p>	<p><u>/</u></p> <p>None:T1 R:T2</p>
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Packing Quantity	
Option	Quantity
None/R	3000 Units/Reel

MARKING

	<p><u>YWWZZX</u></p> <p>LOT NO.</p>
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Characteristics Curves

FIG.1: Max. Allowable LED Forward Current vs. Ambient Temperature

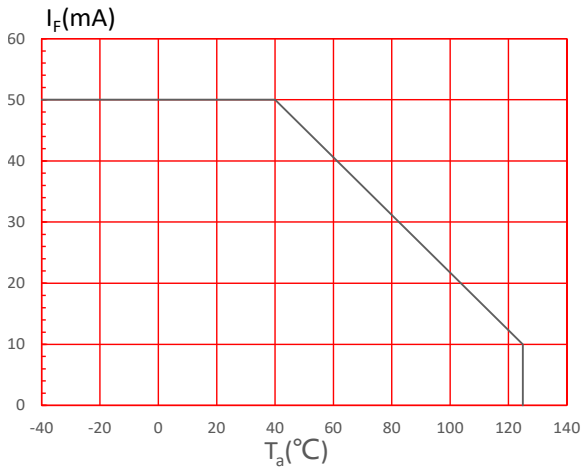


FIG.2: Collector Power Dissipation vs. Ambient Temperature

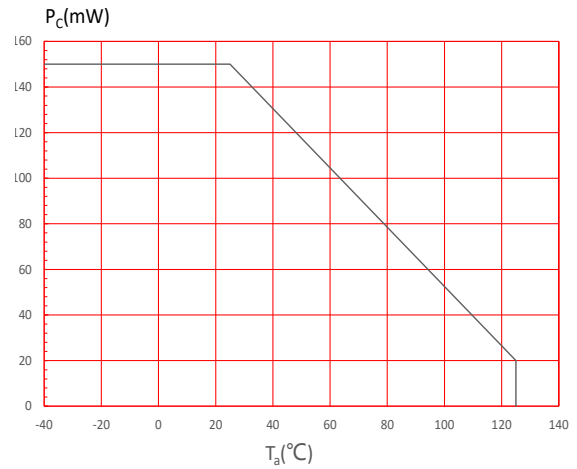


FIG.3: Forward Current vs. Forward Voltage

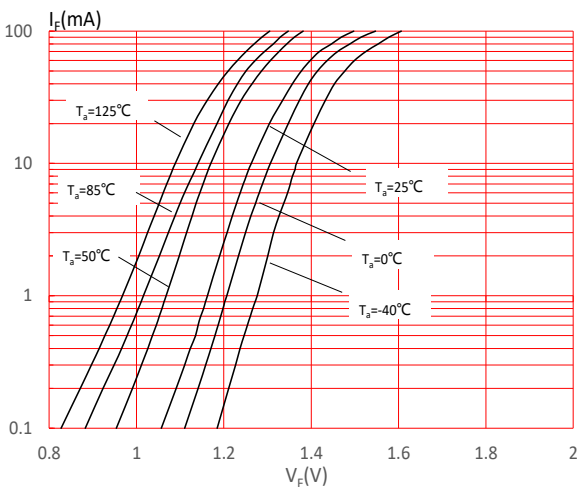


FIG.4: Normalized Collector Dark Current vs. Ambient Temperature

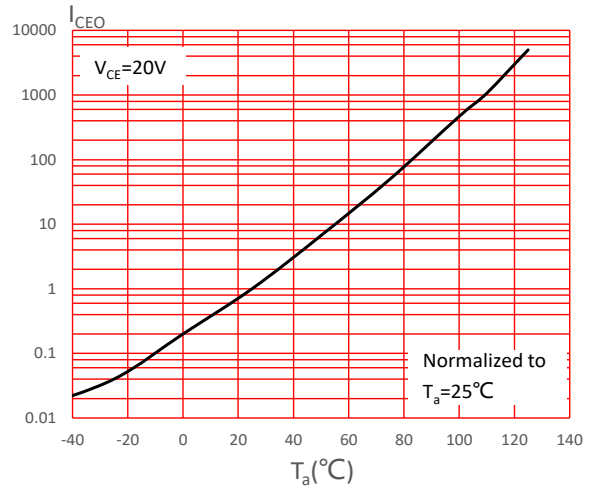


FIG.5: Collector Current vs. Collector-emitter Voltage

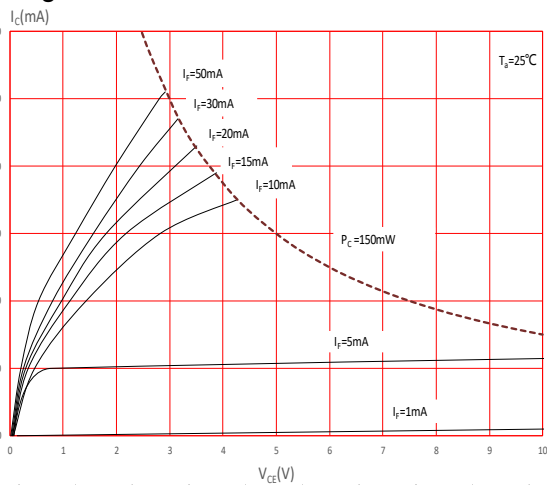


FIG.6: Normalized Current Transfer Ratio vs. Forward Current

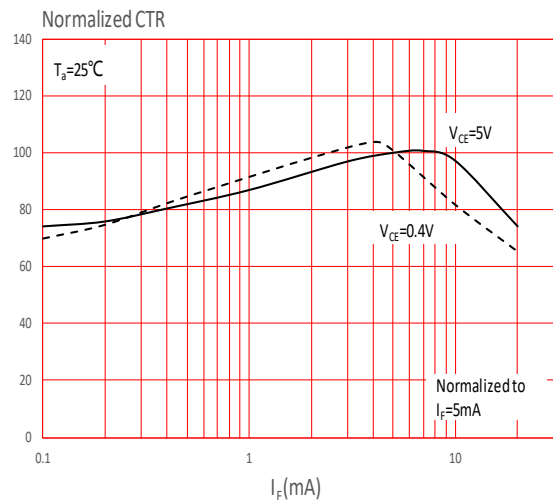


FIG.7: Normalized Current Transfer Ratio vs. Ambient Temperature

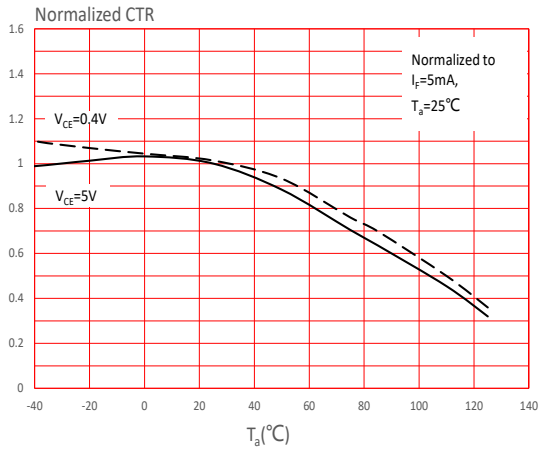


FIG.8: Normalized Collector-emitter Saturation Voltage vs. Ambient Temperature

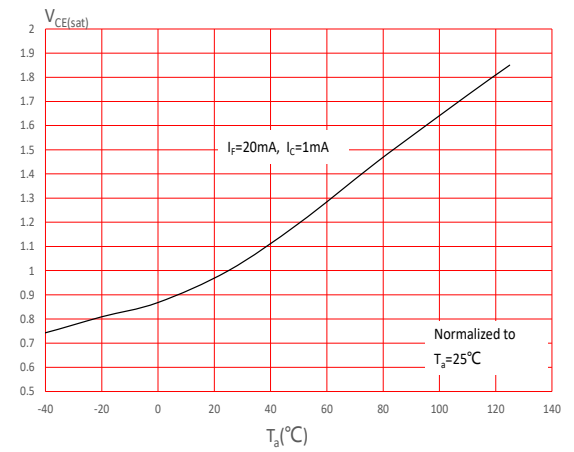


FIG.9: Response Time vs. Load Resistance

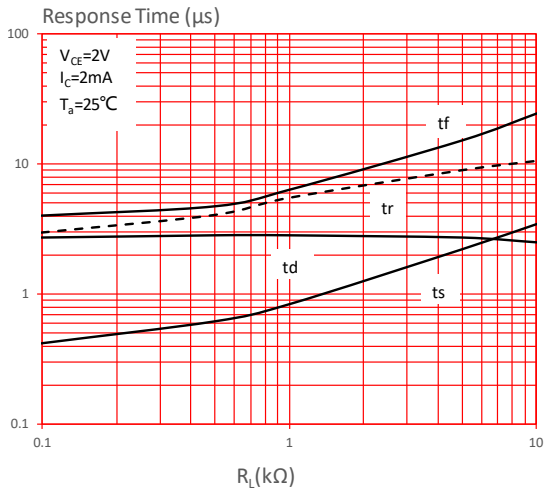
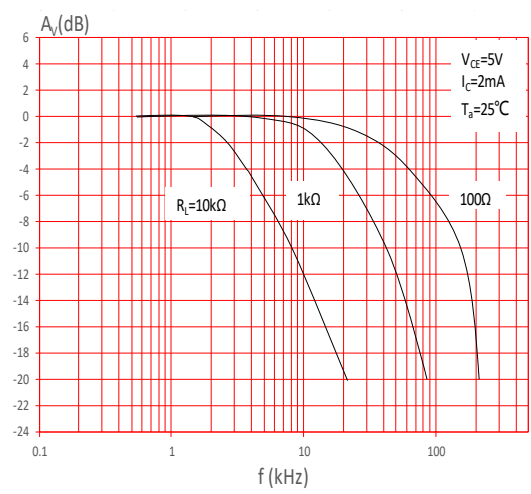


FIG.10: Frequency Response



Test Circuits

FIG.11: Test Circuits of Response Time

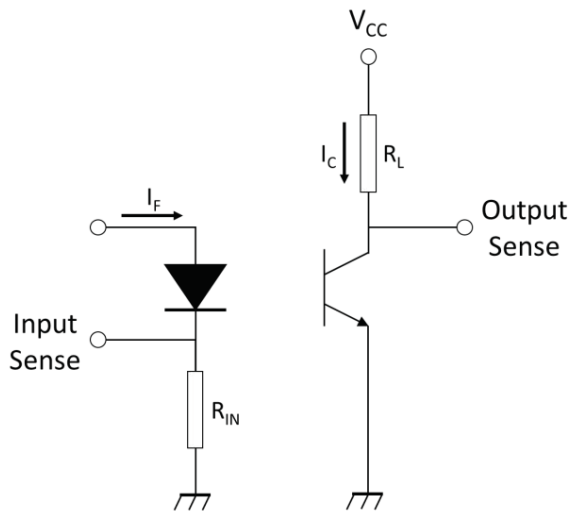


FIG.12: Curves of Response Time

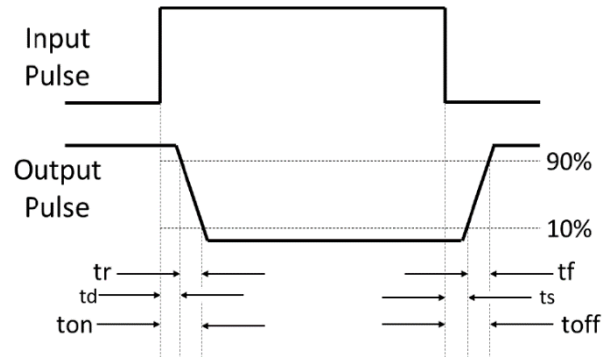
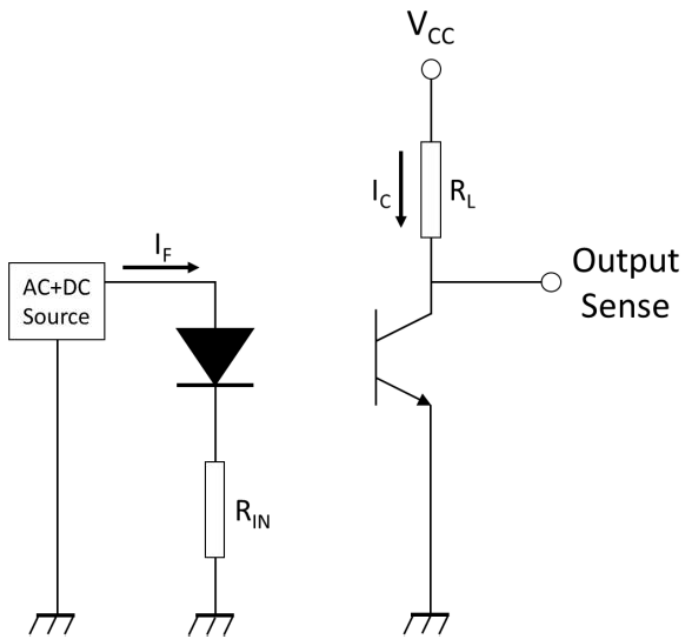
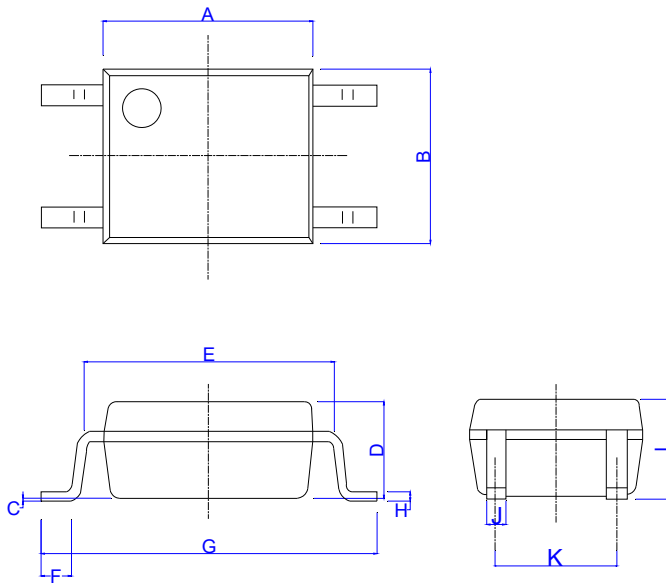


FIG.13: Test Circuits of Frequency Response

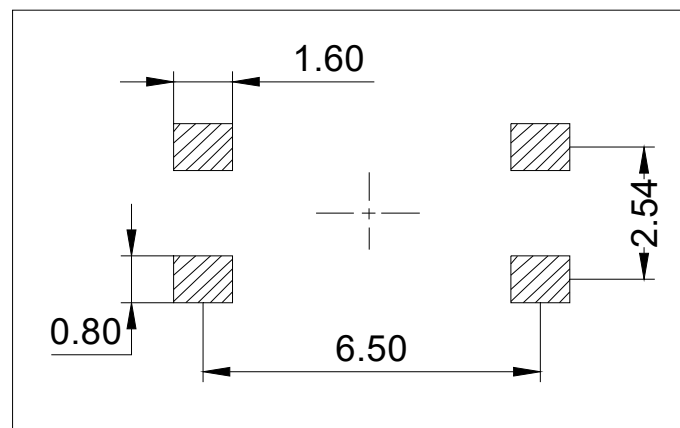


Package Dimension (Unit: mm)



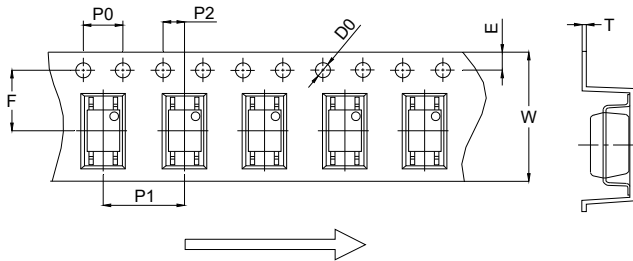
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	3.60		4.20	0.142		0.165
C	0.00		0.20	0.000		0.008
D	1.90		2.30	0.075		0.091
E	5.00		5.60	0.197		0.220
F	0.34		0.94	0.013		0.037
G	6.70		7.30	0.264		0.287
H	0.10		0.30	0.004		0.012
I	2.00		2.40	0.079		0.094
J	0.25		0.55	0.010		0.022
K	2.29		2.79	0.090		0.110

RECOMMENDED SOLDER MASK (Dimensions in mm unless otherwise stated)



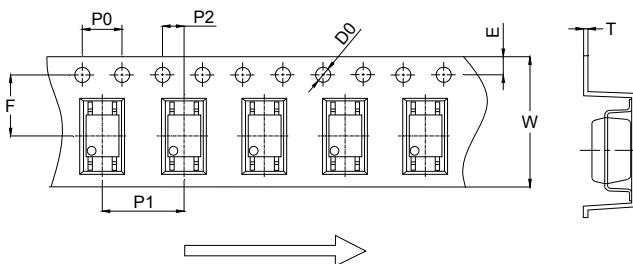
CARRIER TAPE SPECIFICATIONS (Dimensions in mm unless otherwise stated)

Option None



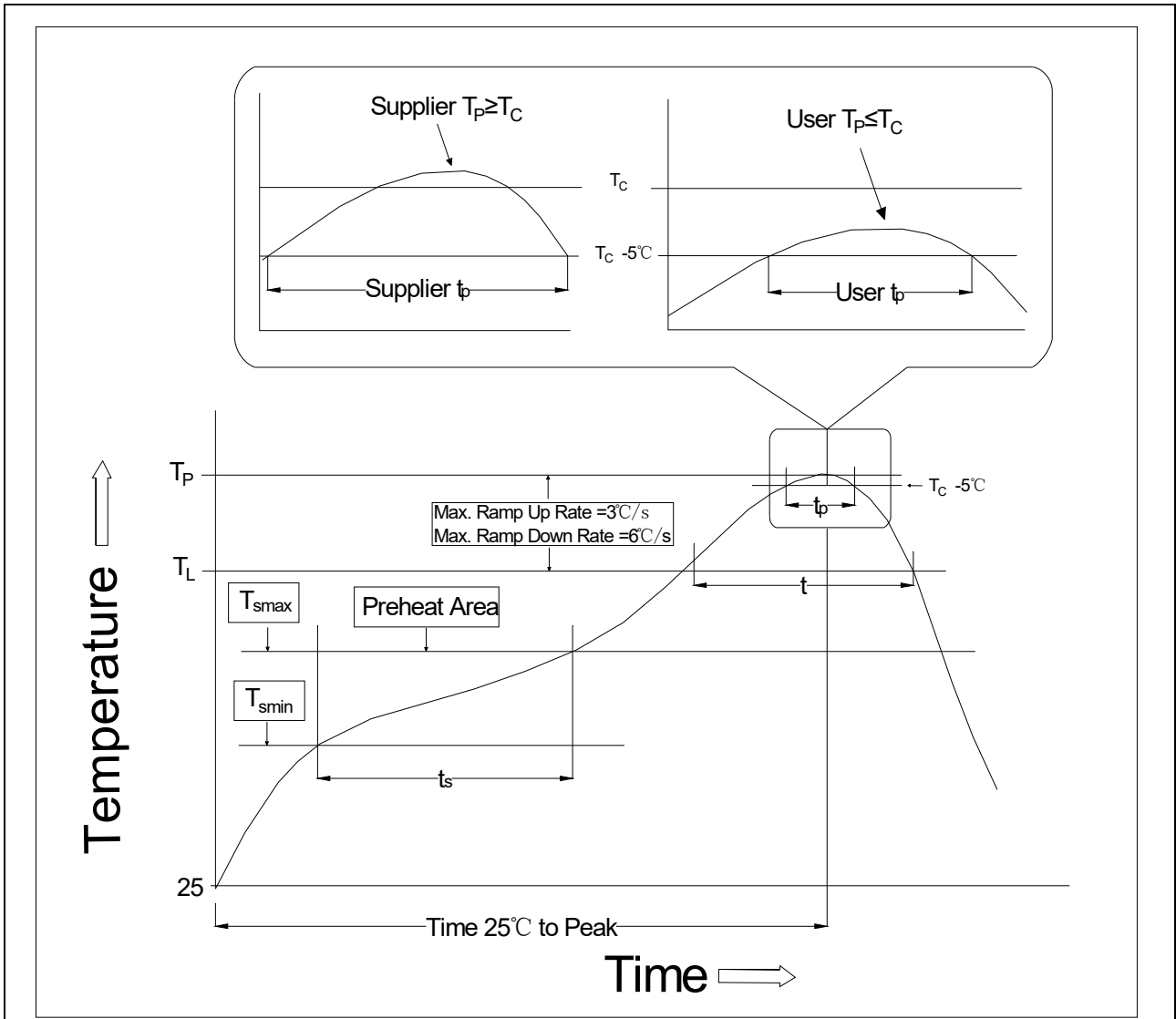
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.60		0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	4.40	4.50	4.60	0.173	0.177	0.181
T	0.25	0.30	0.35	0.010	0.012	0.014
W	11.90	12.00	12.30	0.469	0.472	0.484

Option R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.60		0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	4.40	4.50	4.60	0.173	0.177	0.181
T	0.25	0.30	0.35	0.010	0.012	0.014
W	11.90	12.00	12.30	0.469	0.472	0.484

REFLOW INFORMATION




Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	100	150°C
Temperature Max. (T _{smax})	150	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.	3°C/second max.
Liquidus Temperature (T _L)	183°C	217°C
Time (t _L) Maintained Above (T _L)	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235°C+0°C/-5°C	260°C+0°C/-5°C
Time (t _P) within 5°C of 260°C	20 seconds	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.
2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.
3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.
4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.
5. The component has a shelf life of one year when stored under standard conditions.
6. Recommend storage Temp.: 0~40°C;
Recommend storage humidity: <60%;
MSL level: MSL 1

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